

## SWITCHING REGULATOR APPLICATIONS

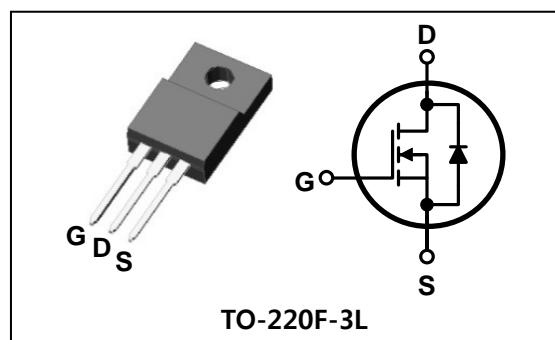
### Features

- High Voltage :  $BV_{DSS}=600V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=14.6pF$ (Typ.)
- Low gate charge :  $Q_g=41nC$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.65\Omega$ (Max.)

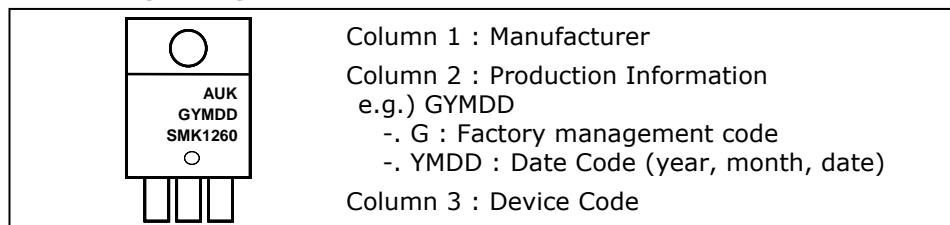
### Ordering Information

Type No.	Marking	Package Code
SMK1260F	SMK1260	TO-220F-3L

### PIN Connection



### Marking Diagram



### Absolute maximum ratings ( $T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	600	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current (DC) *	$I_D$	$T_c=25^\circ C$	A
		$T_c=100^\circ C$	A
Drain current (Pulsed) *	$I_{DM}$	48	A
Power dissipation	$P_D$	45	W
Avalanche current (Single) ②	$I_{AS}$	12	A
Single pulsed avalanche energy ②	$E_{AS}$	549	mJ
Avalanche current (Repetitive) ①	$I_{AR}$	12	A
Repetitive avalanche energy ①	$E_{AR}$	11.6	mJ
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55~150	

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-C)}$	-	2.7	$^\circ C/W$
	$R_{th(J-A)}$	-	62.5	

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

<b>Characteristic</b>	<b>Symbol</b>	<b>Test Condition</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	600	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	$I_{\text{DSS}}$	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{\text{GSS}}$	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance <sup>(④)</sup>	$R_{DS(\text{on})}$	$V_{GS}=10\text{V}, I_D=6.0\text{A}$	-	0.55	0.65	$\Omega$
Forward transfer conductance <sup>(④)</sup>	$g_{fs}$	$V_{DS}=10\text{V}, I_D=6.0\text{A}$	-	10	-	S
Input capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1\text{ MHz}$	-	2162	2882	pF
Output capacitance	$C_{oss}$		-	183	244	
Reverse transfer capacitance	$C_{rss}$		-	14.6	19.4	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=300\text{V}, I_D=12\text{A}$ $R_G=25\Omega$	-	30	-	ns
Rise time	$t_r$		-	85	-	
Turn-off delay time	$t_{d(\text{off})}$		-	140	-	
Fall time	$t_f$		-	90	-	
Total gate charge	$Q_g$	$V_{DS}=480\text{V}, V_{GS}=10\text{V}$ $I_D=12\text{A}$	-	41	63	nC
Gate-source charge	$Q_{gs}$		-	13	-	
Gate-drain charge	$Q_{gd}$		-	10.5	-	

**Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

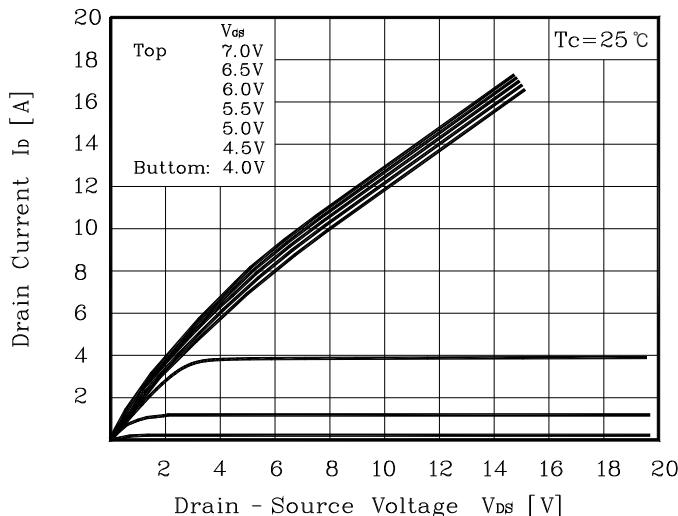
<b>Characteristic</b>	<b>Symbol</b>	<b>Test Condition</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	12	A
Source current (Pulsed) <sup>(①)</sup>	$I_{SM}$		-	-	48	
Forward voltage <sup>(④)</sup>	$V_{SD}$	$V_{GS}=0\text{V}, I_S=12\text{A}$	-	-	1.4	V
Reverse recovery time	$t_{rr}$	$I_S=12\text{A}, V_{GS}=0\text{V}$ $dI_F/dt=100\text{A}/\mu\text{s}$	-	510	-	ns
Reverse recovery charge	$Q_{rr}$		-	4.3	-	$\mu\text{C}$

Note :

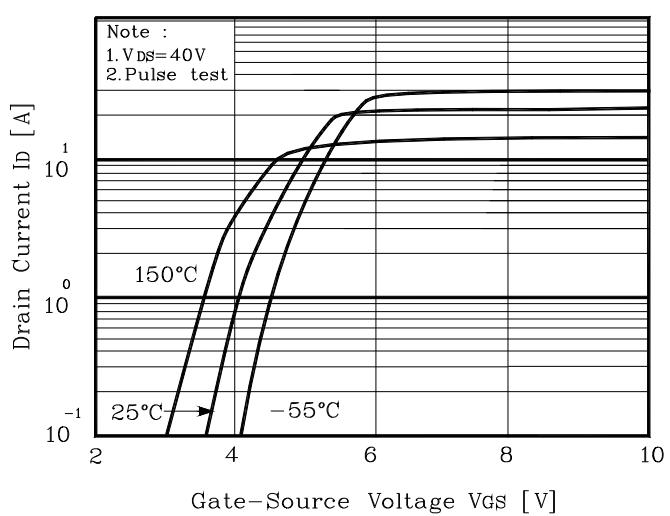
- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ②  $L=7\text{mH}, I_{AS}=12\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

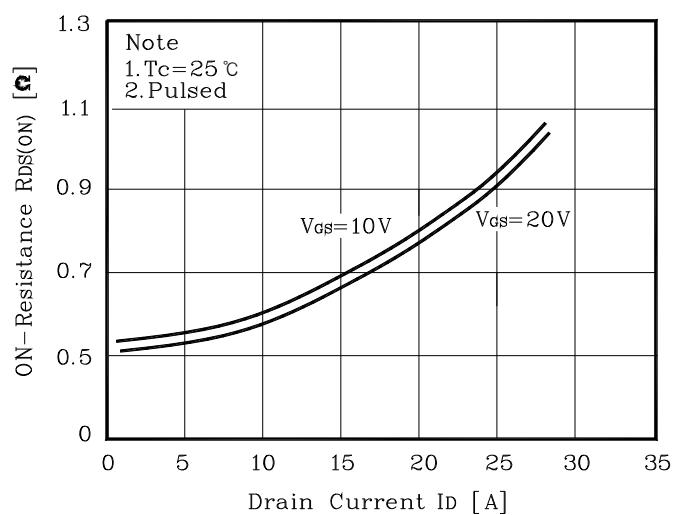
**Fig. 1**  $I_D$  -  $V_{DS}$



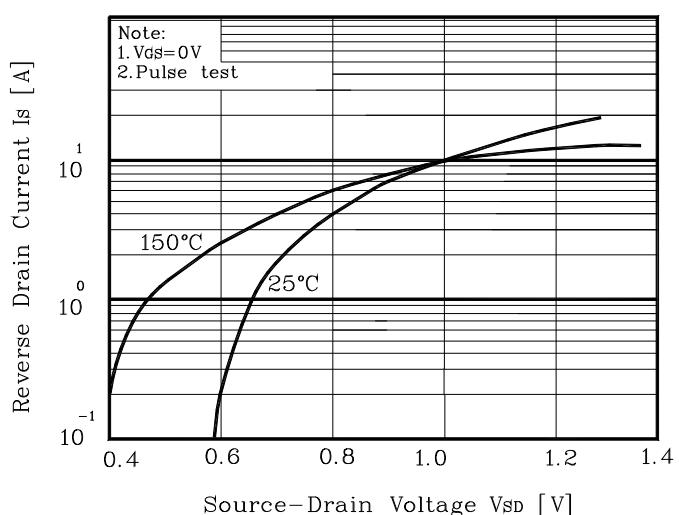
**Fig. 2**  $I_D$  -  $V_{GS}$



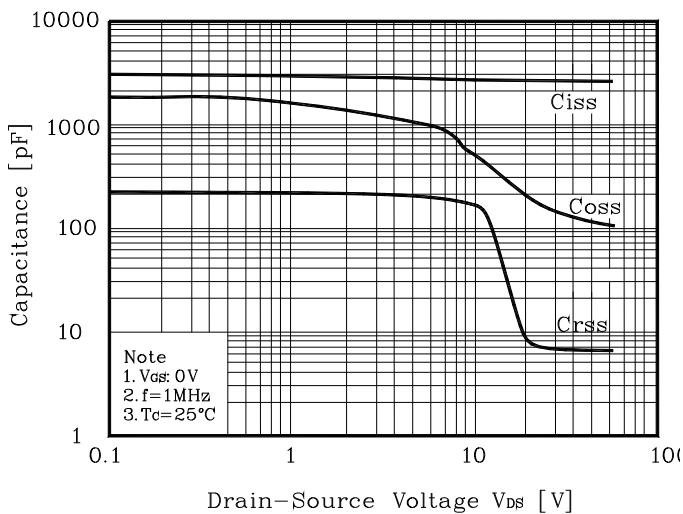
**Fig. 3**  $R_{DS(on)}$  -  $I_D$



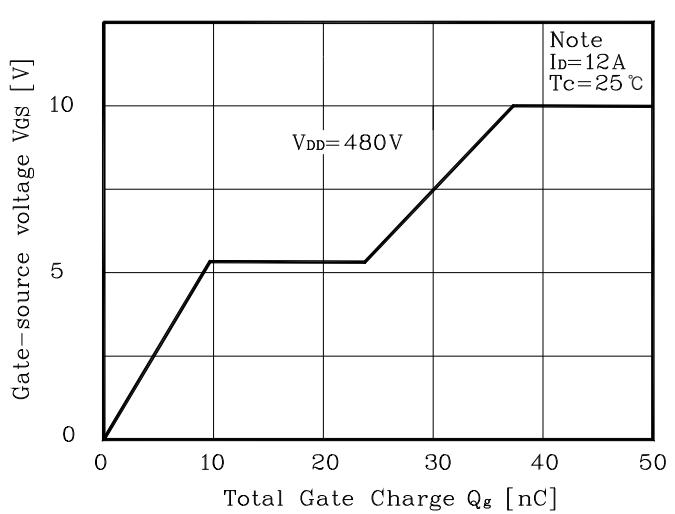
**Fig. 4**  $I_S$  -  $V_{SD}$



**Fig. 5** Capacitance -  $V_{DS}$

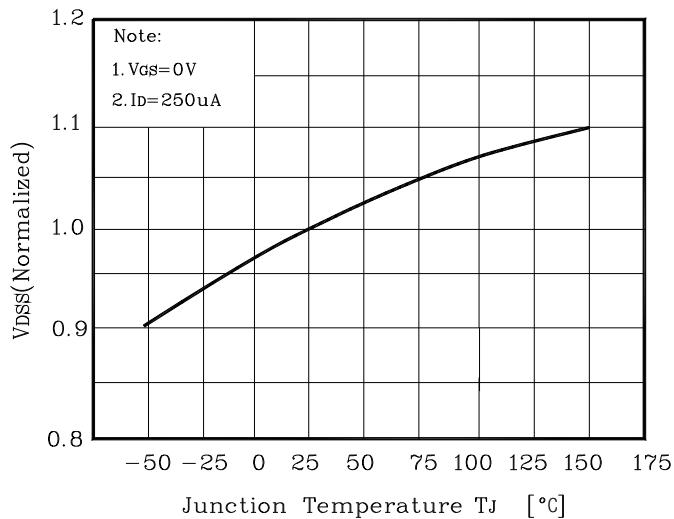


**Fig. 6**  $V_{GS}$  -  $Q_G$

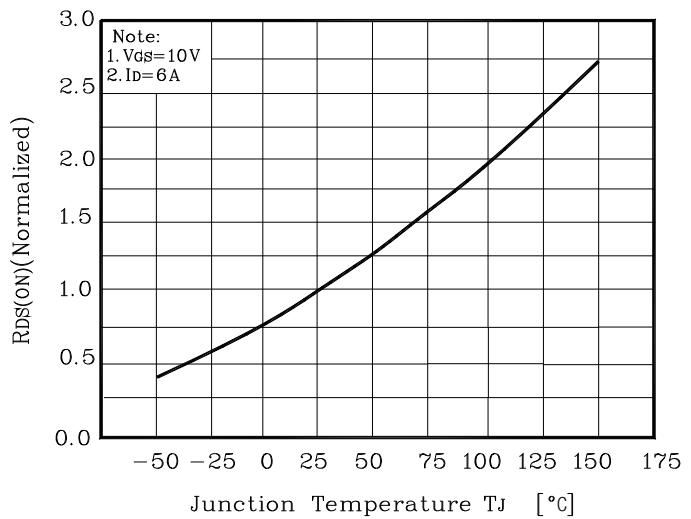


## Electrical Characteristic Curves

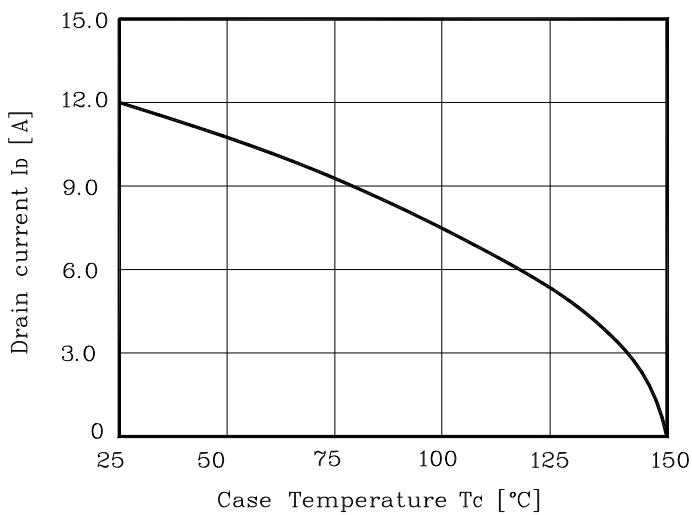
**Fig. 7 V<sub>DSS</sub> - T<sub>J</sub>**



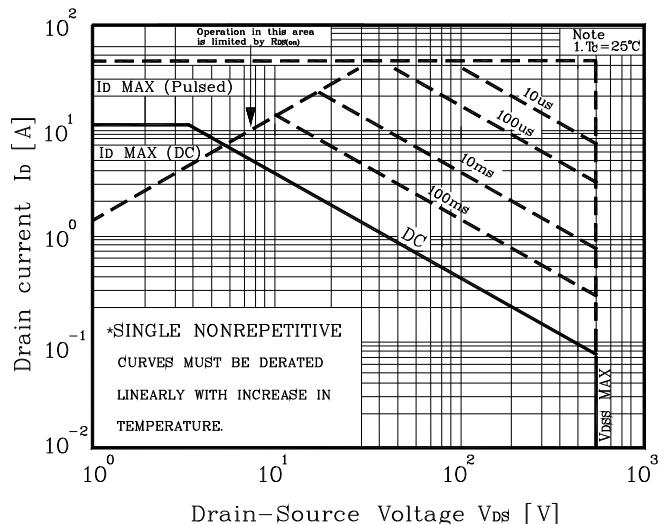
**Fig.8 R<sub>DS(on)</sub> - T<sub>J</sub>**



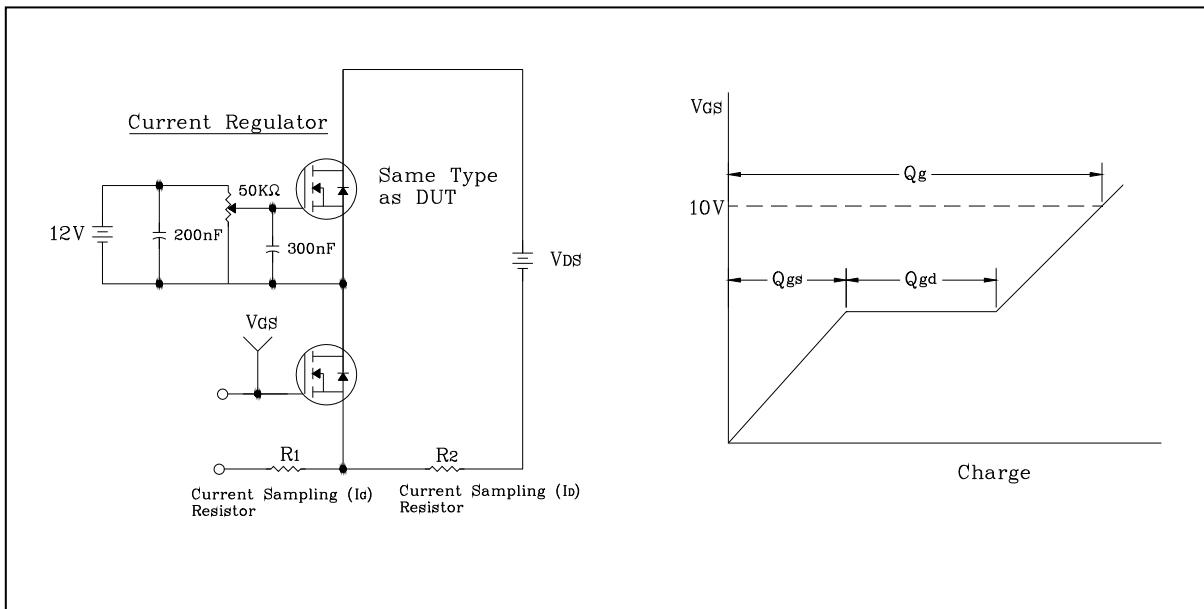
**Fig. 9 I<sub>D</sub> - T<sub>C</sub>**



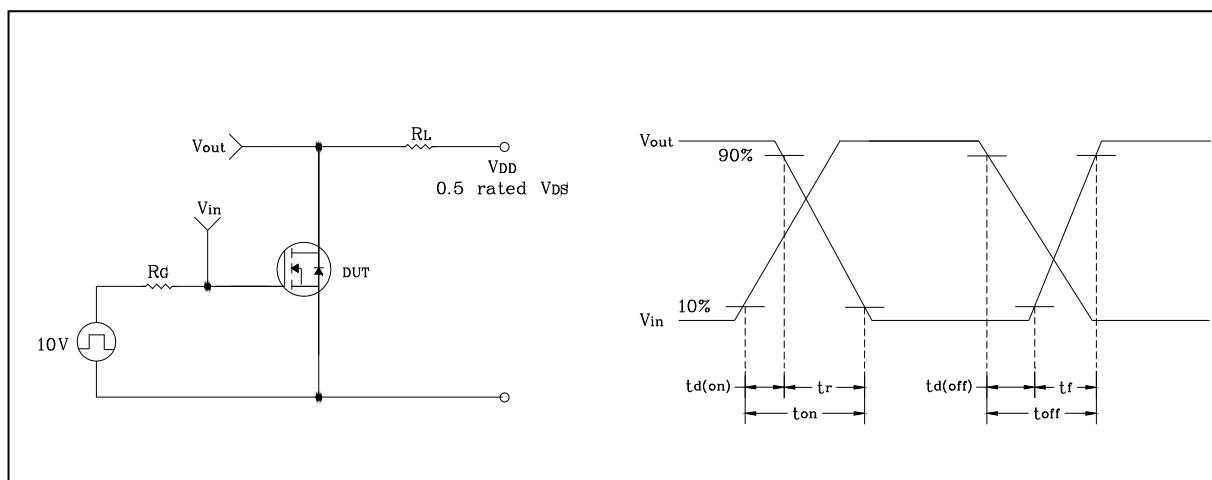
**Fig. 10 Safe Operating Area**



**Fig. 11 Gate Charge Test Circuit & Waveform**



**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

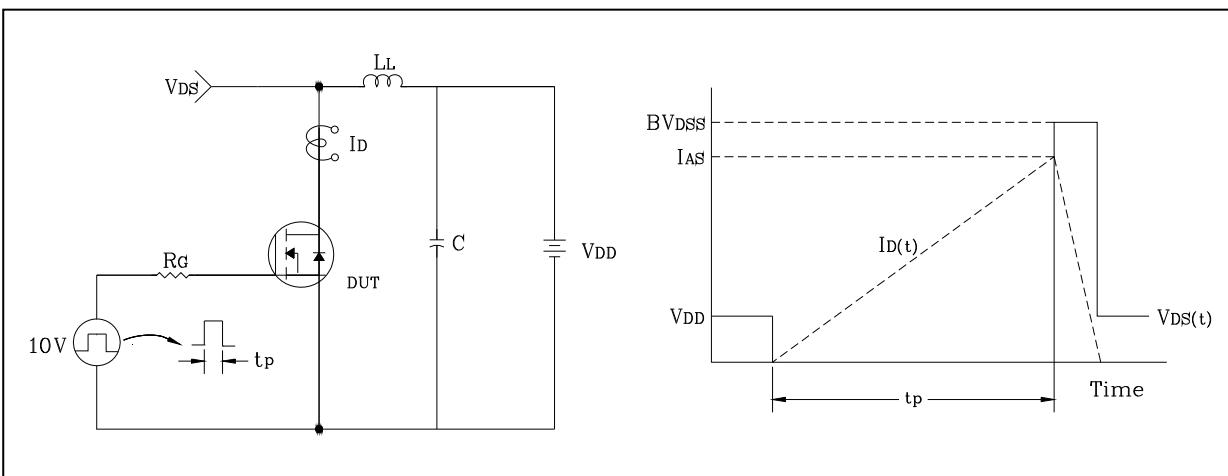
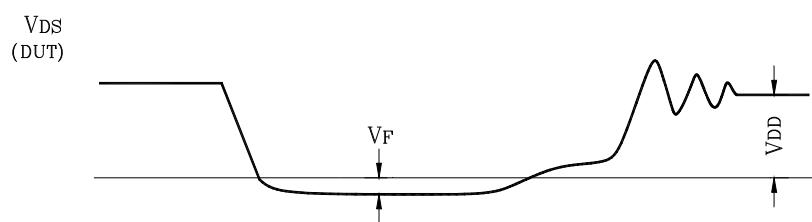
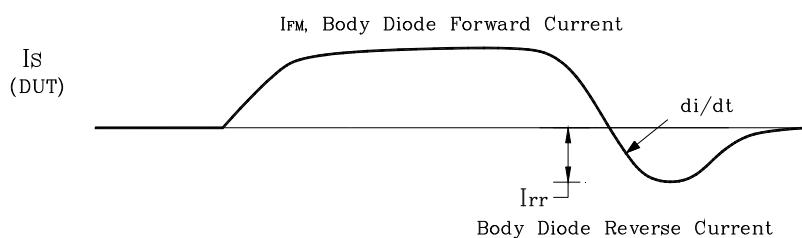
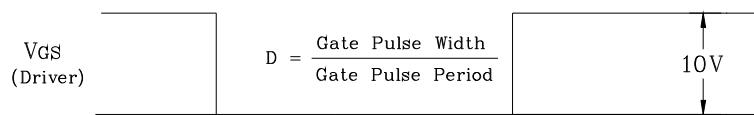
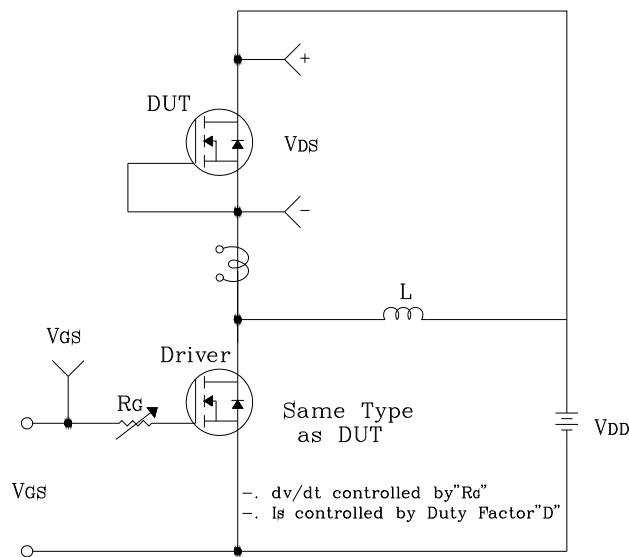
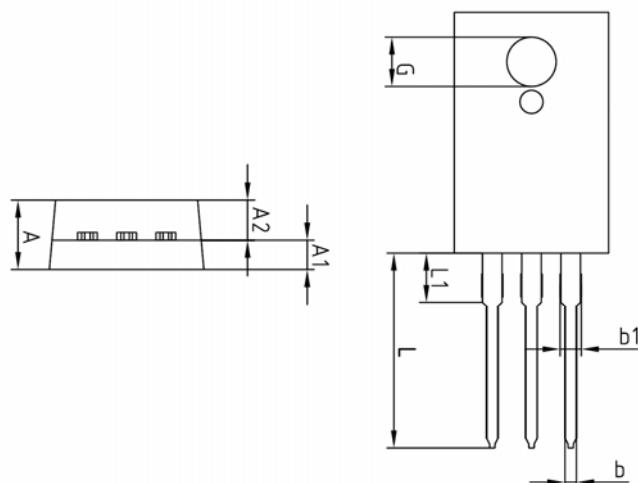
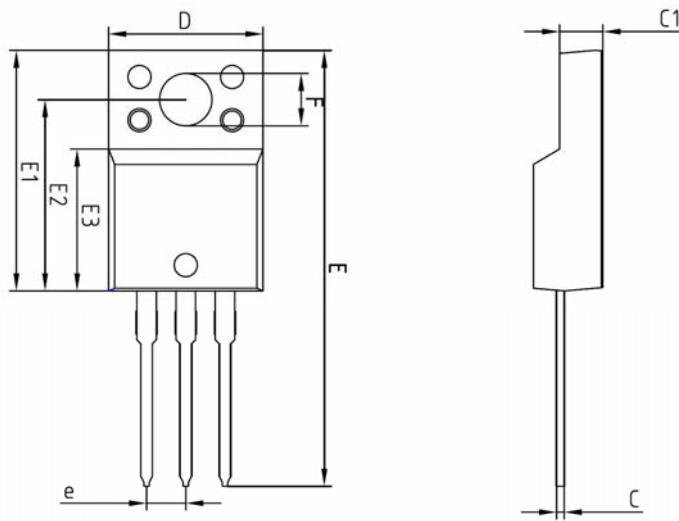


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



**Outline Dimension**

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	—	—	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	—	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	2.54 BSC			
L	12.40	—	13.00	
L1	3.46 BSC			

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